



SPT36-C



TECHNICAL DATA

Silicone Photo-Transistor, SMD package

SPT36-C is a surface mount type photo-transistor containing a chip with 0.6x0.6 mm active area, mounted into a ceramic package and covered with silicone. This device is featuring excellent responsibility of 20 μs and a high photocurrent. It's designed to be easy of setting up optically with a wide angle of half sensitivity of ±40 degrees.

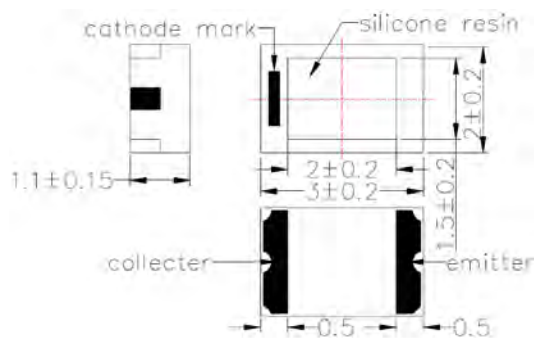
Specifications

- Spectral Responsivity (Peak): 900 nm
- Chip Size: 0.8 x 0.8 mm
- Active Area: 0.6 x 0.6 mm
- Package: SMD
- Type: Ceramics
- Resin Material: Silicone

Absolute Maximum Ratings (T_A=25°C)

Item	Symbol	Value	Unit
C-E Breakdown Voltage	V _{CEO}	30	V
E-C Breakdown Voltage	V _{ECO}	5	V
Collector Current	I _C	10	mA
Collector Dissipation	P _C	50	mW
Operating Temperature	T _{opr}	-25 ... +125	°C
Storage Temperature	T _{stg}	-30 ... +100	°C
Soldering Temperature *1	T _{sol}	240	°C

*1 must be completed within 3 seconds



(Unit: mm)

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Photo Current	I _L	V _{CE} =5V, L=1000Lx	1	3	-	mA
Collector Dark Current	I _D	V _{CE} =5V	-	-	200	nA
Collector-Emitter Satu. Voltage	V _{CE(S)}	I _C =2mA, L=1000Lx	-	-	0.3	V
Spectral Responsivity (Peak)	λ _P		-	900	-	nm
Half Angle of Sensitivity	Θ _{1/2}			±40	-	deg
Rise Time (10-90%)	t _r	R _L =1KΩ, V _R =5V	-	20	-	μs
Fall Time (10-90%)	t _f	I _C =1mA	-	20	-	μs

Note: The above specifications are for reference purpose only and subjected to change without prior notice.